

IN THE CLAIMS:

Applicant proposes to amend claims 1 through 12 herein. Please note that all claims currently pending and under consideration in the referenced application are shown below. Please enter these claims as amended. This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (Currently Amended) A column line structure for use in a cathode assembly of a field emission device, comprising:
an elongated conductive structure;
a resistive layer disposed on a top surface of the elongated conductive structure and extending over at least a portion of one or more side surfaces thereof to form at least one resistive layer side surface; and
an insulative layer disposed over a top surface of the resistive layer having an outer edges-edge substantially aligned with at least one side surfaces of the resistive layer side surface; and
wherein the column line structure is positioned between a substrate and a dielectric layer.
2. (Currently Amended) The column line structure of ~~Claim 1~~Claim 1, wherein the elongated conductive structure comprises metal.
3. (Currently Amended) The column line structure of ~~Claim 1~~Claim 1, wherein the elongated conductive structure comprises aluminum.
4. (Currently Amended) The column line structure of ~~Claim 1~~Claim 1, wherein the resistive layer comprises silicon.
5. (Currently Amended) The column line structure of ~~Claim 1~~Claim 1, wherein the insulative layer comprises silicon oxide.

6. (Currently Amended) The column line structure of ~~Claim 1~~Claim 1, wherein the insulative layer comprises silicon nitride.

7. (Currently Amended) The column line structure of ~~Claim 1~~Claim 1, wherein the insulative layer has a thickness of about 1000 Å.

8. (Currently Amended) A field emission device, comprising a cathode assembly and an anode assembly assembled with the cathode assembly, wherein the cathode assembly includes an addressing matrix comprising multiple row lines elevationally disposed above column lines, the column lines having an insulating layer disposed thereon over a top surface thereof, wherein the insulating layer substantially exactly overlies the column lines and wherein the column lines and the insulating layer are positioned between a substrate and a dielectric layer.

9. (Currently Amended) The field emission device of ~~claim 8~~Claim 8, wherein the column lines include at least one conductive layer and a resistive layer disposed over at least a top surface of the at least one conductive layer.

10. (Currently Amended) The field emission device of ~~claim 9~~Claim 9, wherein the resistive layer extends over at least a portion of at least one side surface of the at least one conductive layer.

11. (Currently Amended) The field emission device of ~~claim 10~~Claim 10, wherein the resistive layer extends over opposing side surfaces of the at least one conductive layer.

12. (Currently Amended) The field emission device of ~~claim 1~~Claim 1, wherein the resistive layer is disposed directly on the top surface of the elongated conductive structure.

13. (Previously Presented) A field emission device, comprising:
a plurality of column line structures, each of the plurality of column line structures comprising:
an elongated conductive structure;
a resistive layer disposed on a top surface of the elongated conductive structure and
extending over at least a portion of one or more side surfaces thereof; and
an insulative layer disposed over a top surface of the resistive layer and having outer
edges substantially aligned with side surfaces of the resistive layer; and
a dielectric layer disposed over at least portions of the plurality of column line structures.

14. (Previously Presented) The field emission device of Claim 13, wherein the
elongated conductive structure comprises metal.

15. (Previously Presented) The field emission device of Claim 13, wherein the
elongated conductive structure comprises aluminum.

16. (Previously Presented) The field emission device of Claim 13, wherein the
resistive layer comprises silicon.

17. (Previously Presented) The field emission device of Claim 13, wherein the
insulative layer comprises silicon oxide.

18. (Previously Presented) The field emission device of Claim 13, wherein the
insulative layer comprises silicon nitride.

19. (Previously Presented) The field emission device of Claim 13, wherein the
insulative layer has a thickness of about 1000 Å.

20. (Previously Presented) The field emission device of Claim 13, wherein the
resistive layer is disposed directly on the top surface of the elongated conductive structure.